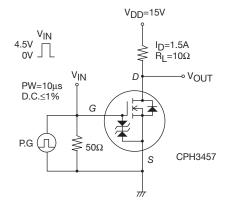
Electrical Characteristics at Ta=25°C

Parameter	Symbol	O an althic a a		Value		
Parameter		Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V 30			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V		1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V		±10	μΑ	
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =1.5A		2.7		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	ID=1.5A, VGS=4.5V		73	95	mΩ
	R _{DS} (on)2	ID=0.75A, VGS=2.5V		95	133	mΩ
	R _{DS} (on)2	ID=0.3A, VGS=1.8V		135	203	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		265		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		35		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz	28			pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.	5.1			ns
Rise Time	tr	See specified Test Circuit.	10			ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.	137			ns
Fall Time	tf	See specified Test Circuit.	36			ns
Total Gate Charge	Qg	V _{DS} =15V, V _{GS} =4.5V, I _D =3A	3.5			nC
Gate-to-Source Charge	Qgs	V _{DS} =15V, V _{GS} =4.5V, I _D =3A	0.57			nC
Gate-to-Drain "Miller" Charge	Qgd	VDS=15V, VGS=4.5V, ID=3A	0.93			nC
Forward Diode Voltage	V _{SD}	IS=3A, VGS=0V		0.87	1.2	V

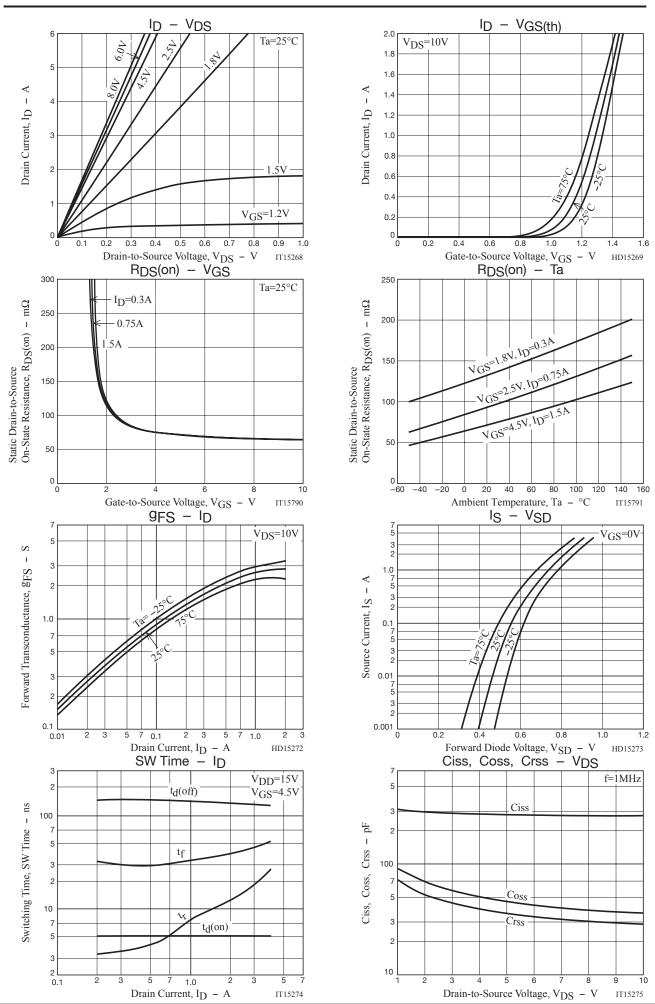
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

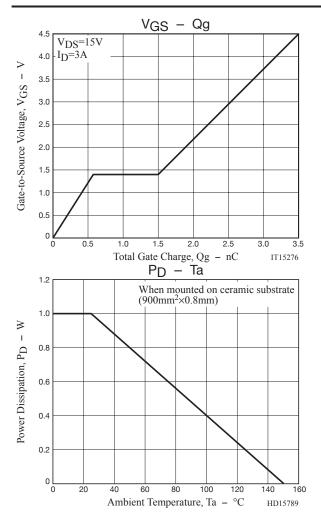
Switching Time Test Circuit

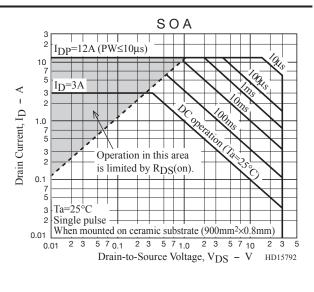


Ordering Information

Device	Package	Shipping	memo	
CPH3457-TL-H	CPH3	3,000pcs./reel	Pb-Free and Halogen Free	
CPH3457-TL-W	CPH3	3,000pcs./reel		

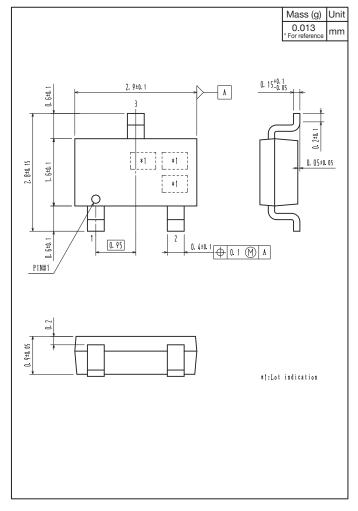




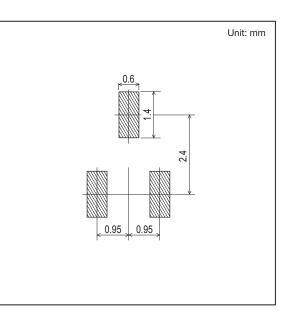


Outline Drawing

СРН3457-ТL-Н, СРН3457-ТL-W



Land Pattern Example



Note on usage : Since the CPH3457 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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